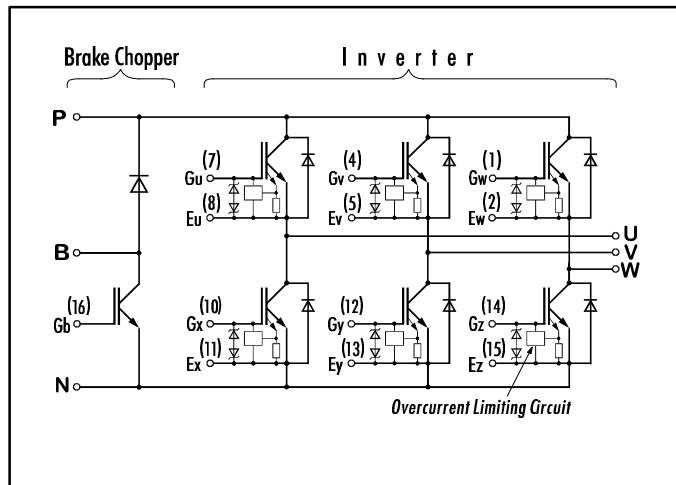


IGBT MODULE (N series)

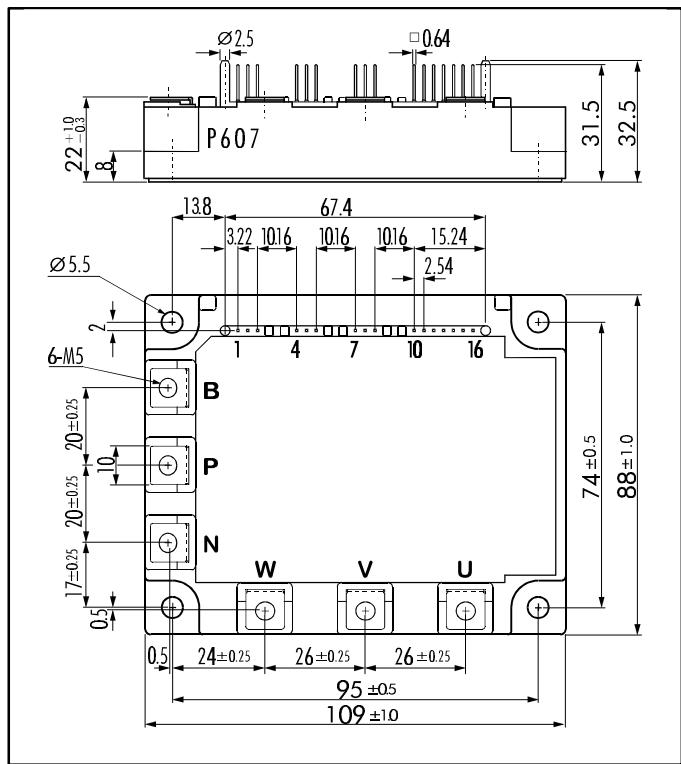
■ Features

- Including Brake Chopper
- Square RBSOA
- Low Saturation Voltage
- Overcurrent Limiting Function
(4 ~ 5 Times Rated Current)

■ Equivalent Circuit



■ Outline Drawing



■ Absolute Maximum Ratings ($T_c=25^\circ\text{C}$)

Items		Symbols	Test Conditions	Ratings	Units
Inverter	Collector-Emitter Voltage	V_{CES}		1200	V
	Gate -Emitter Voltage	V_{GES}		± 20	
Collector Current	I_C	Continuous	50	A	
	$I_{C PULSE}$	1ms	100		
	- $I_{C PULSE}$	Continuous	50		
Collector Power Dissipation	P_C	1 device	400	W	
IGBT	Collector-Emitter Voltage	V_{CES}		1200	V
	Gate -Emitter Voltage	V_{GES}		± 20	
Collector Current	I_C	Continuous	25	A	
	$I_{C PULSE}$	1ms	50		
Collector Power Dissipation	P_C	1 device	200	W	
Brake Chopper FWD	Repetitive Peak Reverse Voltage	V_{RRM}		1200	V
	Average Forward Current	$I_{F(AV)}$		1	A
	Surge Current	I_{FSM}	10ms	50	
	Operating Junction Temperature	T_j		+150	°C
Storage Temperature	T_{Stg}			-40 ~ +125	
Isolation Voltage	V_{ISO}	A.C. 1min.		2500	V
Mounting Screw Torque * ¹				3.5	Nm
Terminal Screw Torque * ¹				3.5	

Note: *1: Recommendable Value; 2.5 ~ 3.5 Nm (M5)

■ Electrical Characteristics (T_j=25°C)

	Items	Symbols	Test Conditions	Min.	Max.	Units
Inverter IGBT	Zero Gate Voltage Collector Current	I _{CES}	V _{GE} =0V V _{CE} =1200V		3.0	mA
	Gate-Emitter Leackage Current	I _{GES}	V _{CE} =0V V _{GE} =± 20V		15	µA
	Gate-Emitter Threshold Voltage	V _{GE(th)}	V _{GE} =20V I _C =50mA	4.5	7.5	V
	Collector-Emitter Saturation Voltage	V _{CE(sat)}	V _{GE} =15V I _C =50A		3.3	
	Input capacitance	C _{ies}	f=1MHz, V _{GE} =0V, V _{CE} =10V	8000 (typ.)		pF
FWD	Turn-on Time	t _{on}	V _{CC} =600V I _C = 50A		1.2	µs
	Turn-off Time	t _{off}				
		t _f	V _{GE} =±15V R _G = 24Ω		1.5	
					0.5	
Brake Chopper IGBT	Diode Forward On-Voltage	V _F	I _F =50A V _{GE} =0V		3.0	V
	Reverse Recovery Time	t _{rr}	I _F =50A; V _{GE} =-10V; -dI/dt=150 A/µs		350	ns
	Zero Gate Voltage Collector Current	I _{CES}	V _{GE} =0V V _{CE} =1200V		1.0	mA
	Gate-Emitter Leackage Current	I _{GES}	V _{CE} =0V V _{GE} =± 20V		100	nA
	Collector-Emitter Saturation Voltage	V _{CE(sat)}	V _{GE} =15V I _C =25A		3.3	V
FWD	Turn-on Time	t _{on}	V _{CC} =600V I _C = 25A		1.2	µs
	Turn-off Time	t _{off}				
		t _f	V _{GE} =±15V R _G = 51Ω		1.5	
					0.5	
	Reverse Current	I _{RRM}	V _R =1200V		1.0	mA
	Reverse Recovery Time	t _{rr}			600	ns

■ Thermal Characteristics

Items	Symbols	Test Conditions	Min.	Max.	Units
Thermal Resistance (1 device)	R _{th(i-c)}	Inverter IGBT		0.31	°C/W
		Inverter FRD		0.85	
		Brake IGBT		0.63	
Contact Thermal Resistance	R _{th(c-f)}	With Thermal Compound	0.05 (typ.)		